TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1009S

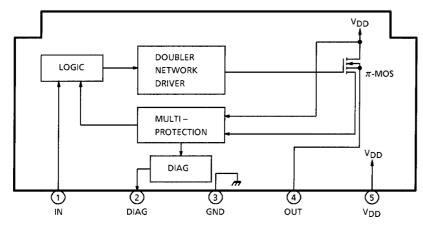
High-side Power Switch for Motors, Solenoids, and Lamp Drivers.

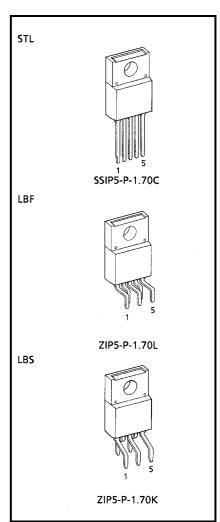
TPD1009S is a monolithic power IC for high–side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit (eg, an MPU). The device offers intelligent self–protection and diagnostic functions.

Features

- A monolithic power IC with a new structure combining a control block (Bi-CMOS) and a vertical power MOS FET (π -MOS) on a single chip.
- One side of load can be grounded to a high-side switch.
- Can directly drive a power load from a microprocessor.
- Built-in protection against thermal shutdown and load short circuiting.
- Incorporates a diagnosis function that allows diagnosis output to be read externally at load short circuiting, opening, or overtemperature.
- Up to -10V of counterelectromotive force from an L load can be applied.
- Low on resistance : $RON = 60m\Omega$ (max)
- Low operating current : IDD = 1mA (typ.) (@VDD = 12V, VIN = 0V)
- 5-pin TO-220 insulated package.
- Three standard lead configurations.

Pin Assignment



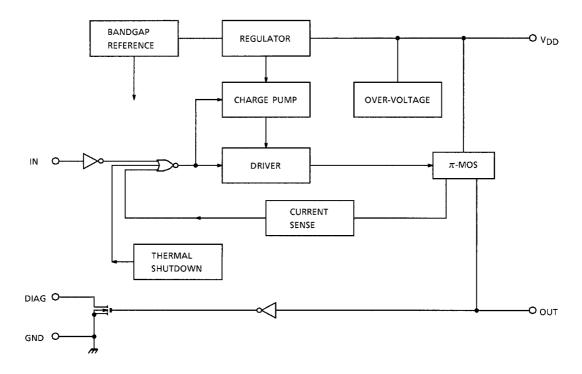


Weight

SSIP5-P-1.70C : 2.1g (typ.) ZIP5-P-1.70L : 2.1g (typ.) ZIP5-P-1.70K : 2.1g (typ.)

Note: That because of its MOS structure, this product is sensitive to static electricity.

Block Diagram

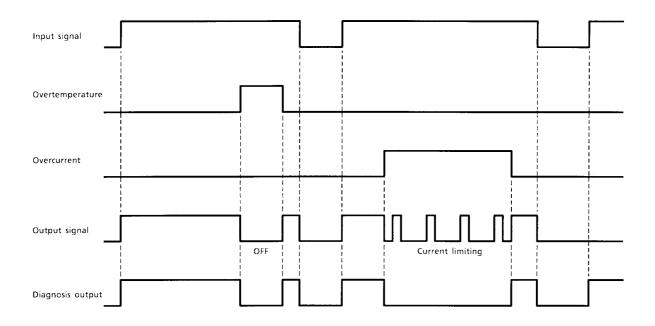


Pin Description

Pin No.	Symbol	Function			
1	IN	Input pin. Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on.			
2	DIAG	Self-diagnosis detection pin. Goes low when overheating is detected or when output is short circuited with input on (high). n-channel open drain.			
3	GND	Ground pin.			
4	OUT	Output pin. When the load is short circuited and current in excess of the detection current flows to the output pin, the output automatically turns on or off.			
5	V _{DD}	Power pin.			

TPD1009S

Timing Chart



Truth Table

Input Signal	Output Signal	Diagnosis Output	State	
Н	Н	Н	Normal	
L	L	L	Nomai	
Н	L	L	Overcurrent	
L	L	L	Overcuitent	
Н	Н	Н	Load open	
L	Н	Н	Load open	
Н	L	L	Overtemperature	
L	L	L	Overtemperature	

Maximum Ratings (Ta = 25°C)

Characteris	tics	Symbol	Rating	Unit	
Drain-source Voltage		V _{DS}	60	V	
Supply Voltage	DC	V _{DD (1)}	25	V	
Supply Voltage	Pulse	V _{DD (2)}	60 (Rs = 1Ω, τ = 250ms)	V	
Input Voltage	DC	V _{IN (1)}	-0.5~12	V	
iliput voltage	Pulse	V _{IN (2)}	V _{DD (1)} + 1.5 (t = 100ms)	V	
Diagnosis Output Volta	ge	V_{DIAG}	-0.5~25	V	
Output Current		Io	Internally Limited	Α	
Input Current		I _{IN}	±10	mA	
Diagnosis Output Curre	ent	I _{DIAG}	5	mA	
Power Dissipation	Tc = 25°C	P _{D (1)}	30	W	
Power Dissipation	Ta = 25°C	P _{D (2)}	2	W	
Operating Temperature		T _{opr}	-40~110	°C	
Junction Temperature		Tj	150	°C	
Storage Temperature		T _{stg}	-55~150	°C	
Lead Temperature/time	,	T _{SOL}	275 (5s), 260 (10s)	°C	

Electrical Characteristics ($T_j = -40\sim110^{\circ}C$, $V_{DD} = 8\sim18V$)

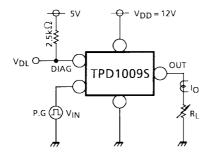
Characteris	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Operating Supply Volta	V _{DD (opr)}	_	_	5	12	18	V	
Supply Current	I _{DD}	_	V _{DD} = 12V, V _{IN} = 0V	_	1	5	mA	
Input Voltage		V _{IH}	_	V _{DD} = 12V, I _O = 8A	3.5	_	_	V
		V _{IL}	_	V _{DD} = 12V, I _O = 1.2mA	_	_	1.5	V
Input Current		I _{IN (1)}	_	V _{DD} = 12V, V _{IN} = 5V	_	50	200	μΑ
		I _{IN (2)}	_	V _{DD} = 12V, V _{IN} = 0V	-0.2	_	0.2	μΑ
On Voltage		V _{DS} (ON)	_	V_{DD} = 12V, I_{O} = 8A, T_{j} = 25°C	_	_	0.48	٧
On Resistance		R _{DS} (ON)	_	V_{DD} = 12V, I_{O} = 8A, T_{j} = 25°C	_	_	0.06	Ω
Output Leakage Current		I _{OL}	_	V _{DD} = 18V, V _{IN} = 0V	_	_	1.2	mA
Diagnosis Output Voltage	"L" Level	V _{DL}	_	V _{DD} = 12V, I _{DL} = 2mA	-	-	0.4	٧
Diagnosis Output Current	"H" Level	I _{DH}	_	V _{DD} = 18V, V _{DH} = 18V	-	-	10	μΑ
Our and Destruction		I _{S (1)} (Note 1)	1	V 12V/ T 25°C	8	12	_	Α
Overcurrent Protection	I _{S (2)} (Note 2)	2	V _{DD} = 12V, T _j = 25°C	15	24	_	Α	
Thermal Shutdown	Temperature	Ts	-	-	150	160	200	°C
Thermal Shutdown	Hysteresis	ΔTs			_	10	_	°C
Open Detection Resist	R _{ops}	_	V _{DD} = 8V	1	50	100	kΩ	
Switching Time		t _{ON}	3	V_{DD} = 12V, R _L = 5Ω, T _j = 25°C	10	200	_	μs
		t _{OFF}	3		10	30		μs

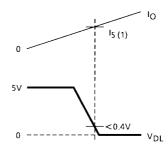
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Note 1: I_{S (1)} Overcurrent detection value when load is short circuited and V_{IN} = "L" \rightarrow "H" Note 2: I_{S (2)} Overcurrent detection value when load current is increased while V_{IN} = "H"

Test Circuit 1

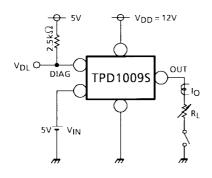
Over-voltage detection

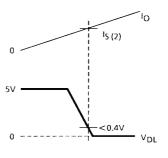




Test Circuit 2

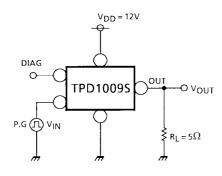
Over-voltage detection

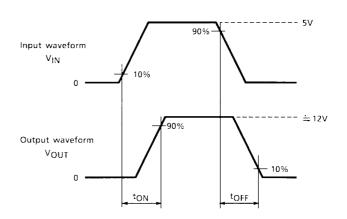


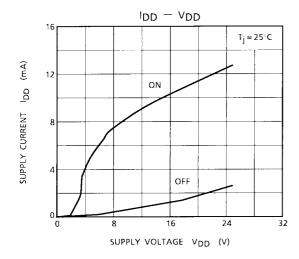


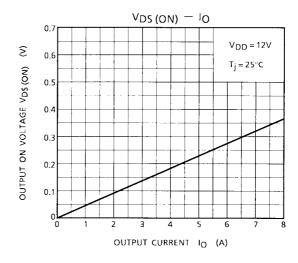
Test Circuit 3

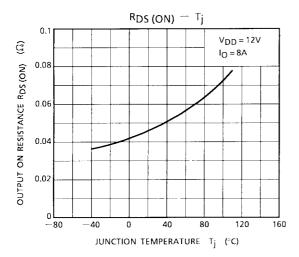
Switching time

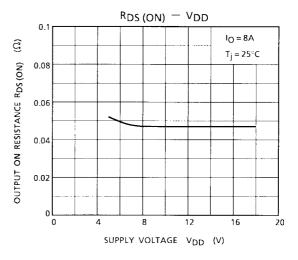


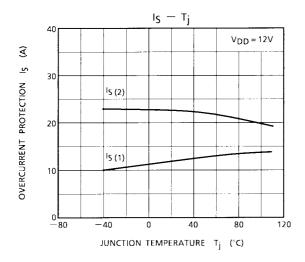


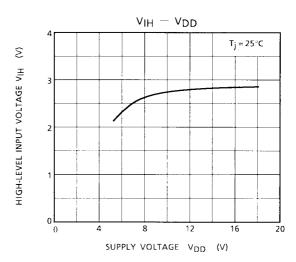


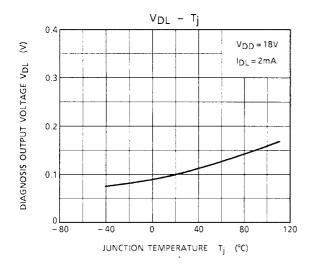


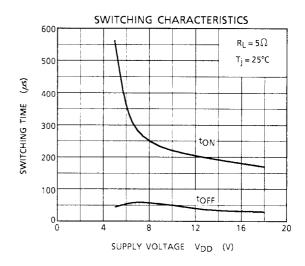


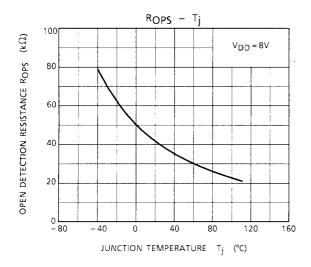


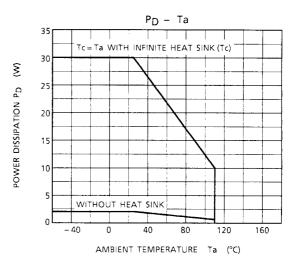


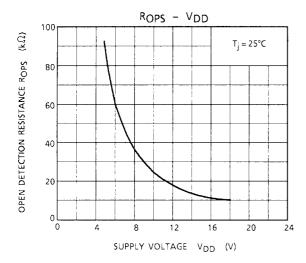










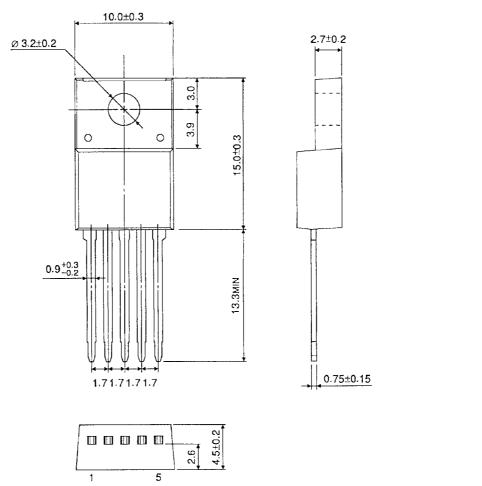


Precaution:

1. Since protection for, for example, reverse connection of the battery is not provided, provide protection using external circuits.

Package Dimensions

SSIP5-P-1.70C (STL)
Unit: mm



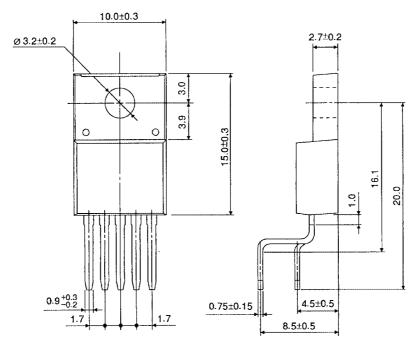
Weight: 2.1g (typ.)

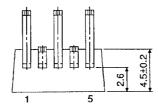
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Package Dimensions

ZIP5-P-1.70L (LBF)



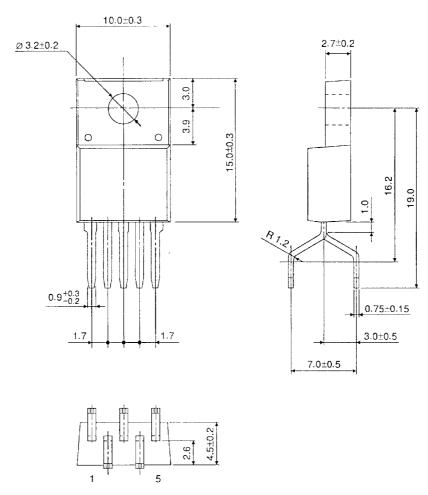




Weight: 2.1g (typ.)

Package Dimensions

ZIP5-P-1.70K (LBS) Unit: mm



Weight: 2.1g (typ.)

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